



# THE DATASHEET OF PSMN1R6-30MLHX





# PSMN1R6-30MLH

N-channel 30 V, 1.9 m $\Omega$ , 160 A logic level MOSFET in LFAK33 using NextPowerS3 technology

12 November 2019

Product data sheet

## 1. General description

Logic level gate drive N-channel enhancement mode MOSFET in LFAK33 package. NextPowerS3 technology delivers low  $R_{DSon}$ , low  $I_{DSS}$  leakage and high efficiency. Rated to 160 A and optimized for DC load switch and hot-swap applications.

## 2. Features and benefits

- Optimized for low  $R_{DSon}$
- Low leakage < 1  $\mu$ A at 25 °C
- Low spiking and ringing for low EMI designs
- Optimized for 4.5 V gate drive
- 160 A rated
- High reliability copper-clip bonded and solder die attach LFAK33 package
- Qualified to 175 °C
- Exposed leads for optimal visual solder inspection

## 3. Applications

- DC switch / load switch
- USB-PD and fast-charge
- Battery protection
- OR-ing and hot-swap
- Synchronous rectifier in AC-DC and DC-DC applications
- Brushed and BLDC (brushless) motor control

## 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{DS}$	drain-source voltage	25 °C $\leq$ $T_j$ $\leq$ 175 °C	-	-	30	V
$I_D$	drain current	$V_{GS} = 10$ V; $T_{mb} = 25$ °C; <a href="#">Fig. 2</a>	[1]	-	160	A
$P_{tot}$	total power dissipation	$T_{mb} = 25$ °C; <a href="#">Fig. 1</a>	-	-	106	W
$T_j$	junction temperature		-55	-	175	°C
<b>Static characteristics</b>						
$R_{DSon}$	drain-source on-state resistance	$V_{GS} = 10$ V; $I_D = 25$ A; $T_j = 25$ °C; <a href="#">Fig. 10</a>	-	1.6	1.9	m $\Omega$
		$V_{GS} = 4.5$ V; $I_D = 25$ A; $T_j = 25$ °C; <a href="#">Fig. 10</a>	-	2	2.6	m $\Omega$
<b>Dynamic characteristics</b>						
$Q_{GD}$	gate-drain charge	$I_D = 25$ A; $V_{DS} = 15$ V; $V_{GS} = 4.5$ V; <a href="#">Fig. 12</a> ; <a href="#">Fig. 13</a>	1.3	7	14	nC

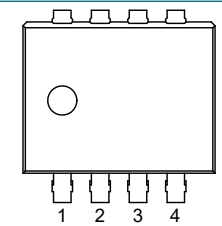
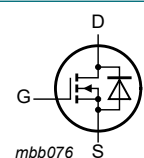
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Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$Q_{G(\text{tot})}$	total gate charge	$I_D = 25 \text{ A}$ ; $V_{DS} = 15 \text{ V}$ ; $V_{GS} = 10 \text{ V}$ ; <a href="#">Fig. 12</a> ; <a href="#">Fig. 13</a>	18	41	68	nC
<b>Source-drain diode</b>						
S	softness factor	$I_S = 20 \text{ A}$ ; $di_S/dt = -100 \text{ A}/\mu\text{s}$ ; $V_{GS} = 0 \text{ V}$ ; $V_{DS} = 15 \text{ V}$ ; <a href="#">Fig. 16</a>	-	0.7	-	

[1] 160A Continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.

## 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	 <p>LPAK33 (SOT1210)</p>	 <p>mbb076</p>
2	S	source		
3	S	source		
4	G	gate		
mb	D	mounting base; connected to drain		

## 6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN1R6-30MLH	LPAK33	Plastic, single ended surface mounted package (LPAK33); 8 leads; 0.65 mm pitch	SOT1210

## 7. Marking

Table 4. Marking codes

Type number	Marking code
PSMN1R6-30MLH	1H630L

## 8. Limiting values

Table 5. Limiting values

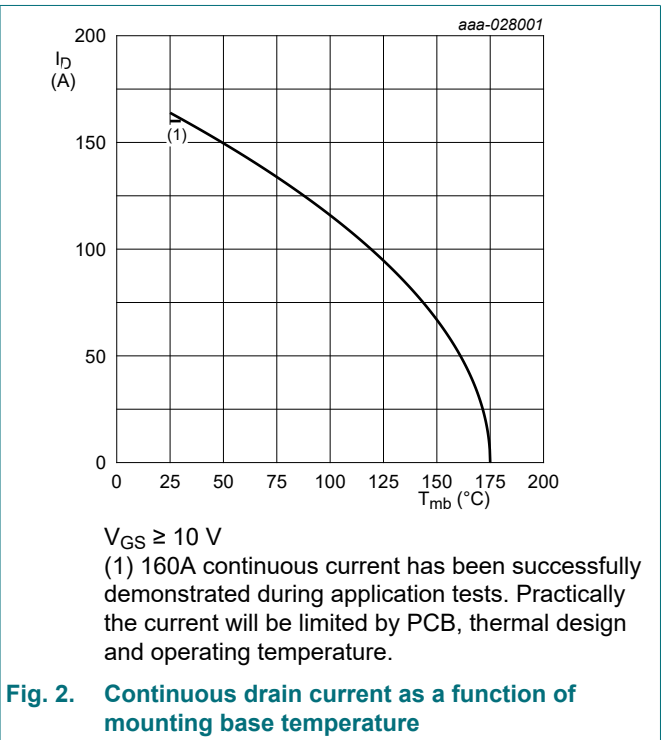
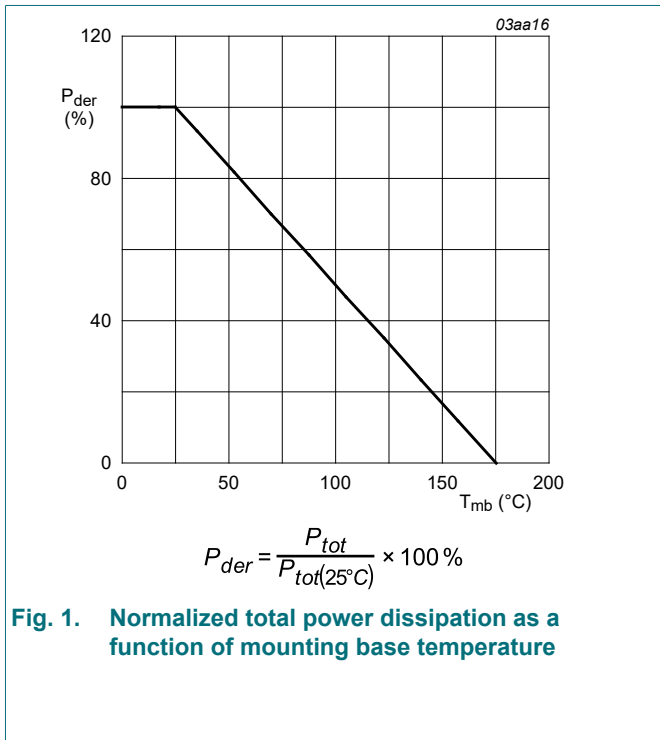
In accordance with the Absolute Maximum Rating System (IEC 60134).

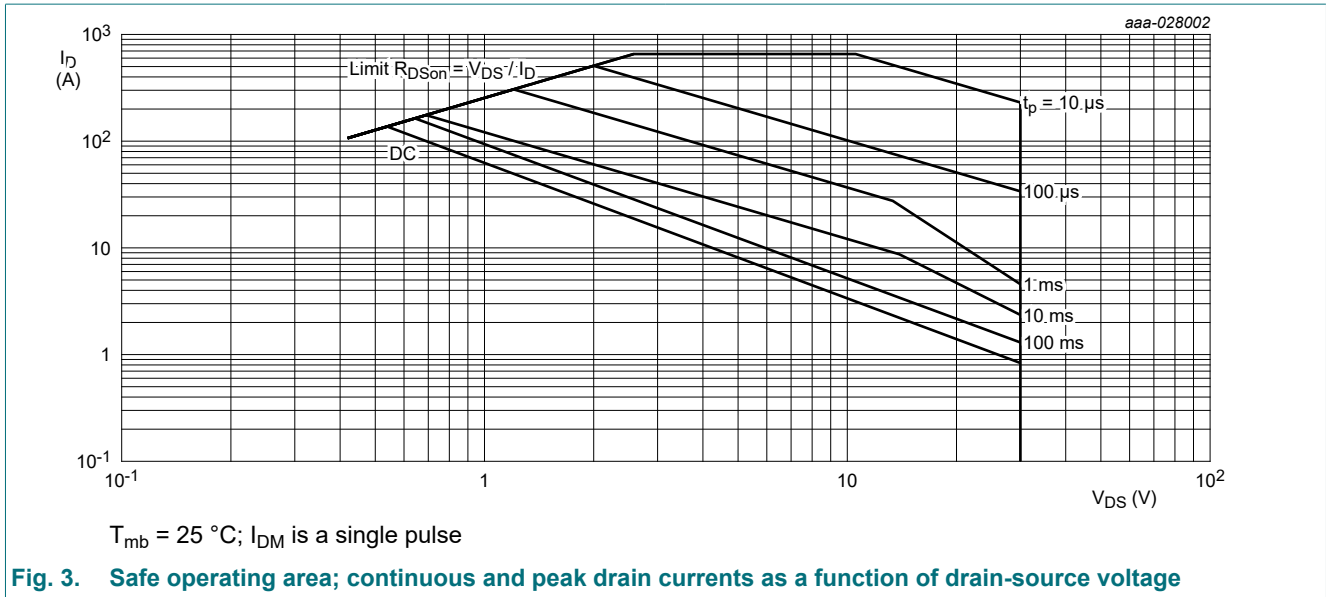
Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DS}$	drain-source voltage	$25 \text{ }^\circ\text{C} \leq T_j \leq 175 \text{ }^\circ\text{C}$	-	30	V
$V_{DGR}$	drain-gate voltage	$25 \text{ }^\circ\text{C} \leq T_j \leq 175 \text{ }^\circ\text{C}$ ; $R_{GS} = 20 \text{ k}\Omega$	-	30	V
$V_{GS}$	gate-source voltage		-20	20	V
$P_{\text{tot}}$	total power dissipation	$T_{\text{mb}} = 25 \text{ }^\circ\text{C}$ ; <a href="#">Fig. 1</a>	-	106	W
$I_D$	drain current	$V_{GS} = 10 \text{ V}$ ; $T_{\text{mb}} = 25 \text{ }^\circ\text{C}$ ; <a href="#">Fig. 2</a>	[1]	160	A
		$V_{GS} = 10 \text{ V}$ ; $T_{\text{mb}} = 100 \text{ }^\circ\text{C}$ ; <a href="#">Fig. 2</a>		116	A
$I_{DM}$	peak drain current	pulsed; $t_p \leq 10 \text{ } \mu\text{s}$ ; $T_{\text{mb}} = 25 \text{ }^\circ\text{C}$ ; <a href="#">Fig. 3</a>	-	656	A

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Symbol	Parameter	Conditions	Min	Max	Unit
T <sub>stg</sub>	storage temperature		-55	175	°C
T <sub>j</sub>	junction temperature		-55	175	°C
T <sub>slid(M)</sub>	peak soldering temperature		-	260	°C
<b>Source-drain diode</b>					
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C	-	106	A
I <sub>SM</sub>	peak source current	pulsed; t <sub>p</sub> ≤ 10 μs; T <sub>mb</sub> = 25 °C	-	656	A
<b>Avalanche ruggedness</b>					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	I <sub>D</sub> = 25 A; V <sub>sup</sub> ≤ 30 V; R <sub>GS</sub> = 50 Ω; V <sub>GS</sub> = 10 V; T <sub>j(init)</sub> = 25 °C; unclamped; t <sub>p</sub> = 797 μs	[2]	-	388 mJ
I <sub>AS</sub>	non-repetitive avalanche current	V <sub>sup</sub> ≤ 30 V; V <sub>GS</sub> = 10 V; T <sub>j(init)</sub> = 25 °C; R <sub>GS</sub> = 50 Ω	[2]	-	87 A

- [1] 160A Continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.
- [2] Protected by 100% test

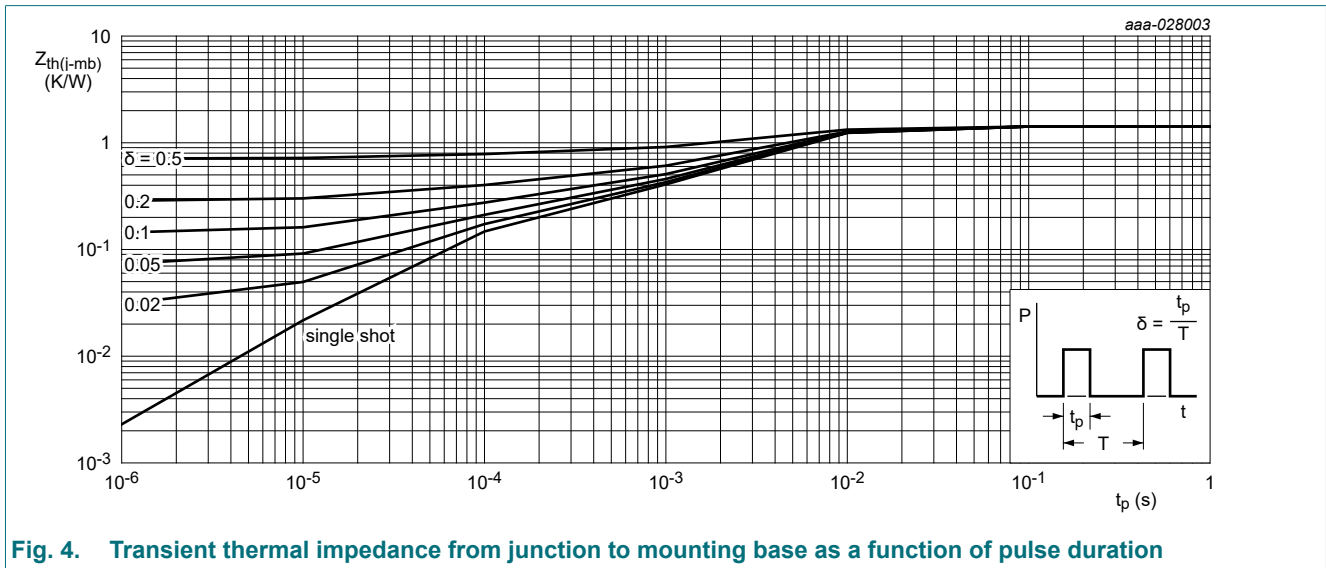




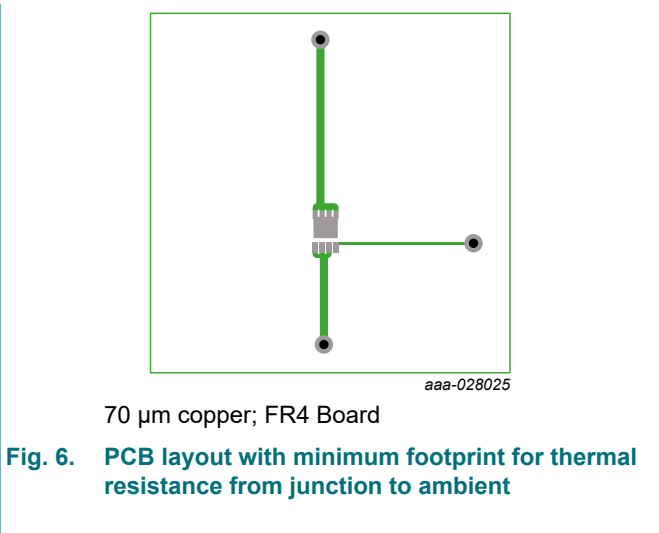
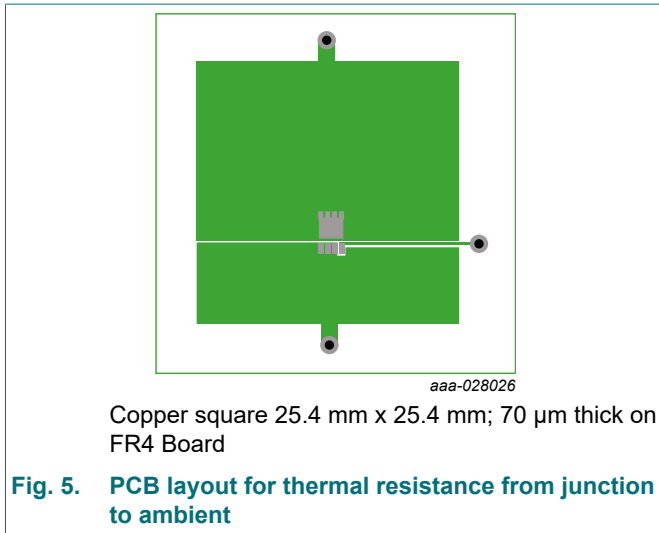
### 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	Fig. 4	-	1.12	1.42	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	Fig. 5	-	50	-	K/W
		Fig. 6	-	130	-	K/W



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## 10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$	30	-	-	V
		$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 \text{ }^\circ C$	27	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ }^\circ C$	1.2	1.6	2.2	V
$\Delta V_{GS(th)}/\Delta T$	gate-source threshold voltage variation with temperature	$25 \text{ }^\circ C \leq T_j \leq 150 \text{ }^\circ C$	-	-3.8	-	mV/K
$I_{DSS}$	drain leakage current	$V_{DS} = 24 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ C$	-	-	1	μA
		$V_{DS} = 24 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 125 \text{ }^\circ C$	-	2.2	-	μA
$I_{GSS}$	gate leakage current	$V_{GS} = 16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ C$	-	-	100	nA
		$V_{GS} = -16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ C$	-	-	100	nA
$R_{DSon}$	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ }^\circ C;$ <a href="#">Fig. 10</a>	-	1.6	1.9	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 150 \text{ }^\circ C;$ <a href="#">Fig. 11</a>	-	-	3.5	mΩ
		$V_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ }^\circ C;$ <a href="#">Fig. 10</a>	-	2	2.6	mΩ
		$V_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A}; T_j = 150 \text{ }^\circ C;$ <a href="#">Fig. 11</a>	-	-	4.8	mΩ
$R_G$	gate resistance	$f = 1 \text{ MHz}$	1.3	3.3	8.3	Ω
<b>Dynamic characteristics</b>						
$Q_{G(tot)}$	total gate charge	$I_D = 25 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 4.5 \text{ V};$ <a href="#">Fig. 12; Fig. 13</a>	8.9	20	33	nC
		$I_D = 25 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 10 \text{ V};$ <a href="#">Fig. 12; Fig. 13</a>	18	41	68	nC
		$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$	-	21	-	nC

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Symbol	Parameter	Conditions	Min	Typ	Max	Unit	
$Q_{GS}$	gate-source charge	$I_D = 25\text{ A}; V_{DS} = 15\text{ V}; V_{GS} = 4.5\text{ V};$ <a href="#">Fig. 12</a> ; <a href="#">Fig. 13</a>	1.5	5.7	11	nC	
$Q_{GS(th)}$	pre-threshold gate-source charge		1	3.6	6.8	nC	
$Q_{GS(th-pl)}$	post-threshold gate-source charge		0.6	2.1	4.1	nC	
$Q_{GD}$	gate-drain charge		1.3	7	14	nC	
$V_{GS(pl)}$	gate-source plateau voltage	$I_D = 25\text{ A}; V_{DS} = 15\text{ V};$ <a href="#">Fig. 12</a> ; <a href="#">Fig. 13</a>	-	2.6	-	V	
$C_{iss}$	input capacitance	$V_{DS} = 15\text{ V}; V_{GS} = 0\text{ V}; f = 1\text{ MHz};$ $T_j = 25\text{ }^\circ\text{C};$ <a href="#">Fig. 14</a>	1421	2369	3554	pF	
$C_{oss}$	output capacitance		455	758	1137	pF	
$C_{rss}$	reverse transfer capacitance		59	217	521	pF	
$t_{d(on)}$	turn-on delay time	$V_{DS} = 15\text{ V}; R_L = 0.6\text{ }\Omega; V_{GS} = 4.5\text{ V};$ $R_{G(ext)} = 5\text{ }\Omega$	-	17	-	ns	
$t_r$	rise time		-	34	-	ns	
$t_{d(off)}$	turn-off delay time		-	32	-	ns	
$t_f$	fall time		-	24	-	ns	
$Q_{oss}$	output charge	$V_{GS} = 0\text{ V}; V_{DS} = 15\text{ V}; f = 1\text{ MHz};$ $T_j = 25\text{ }^\circ\text{C}$	-	18.7	-	nC	
<b>Source-drain diode</b>							
$V_{SD}$	source-drain voltage	$I_S = 20\text{ A}; V_{GS} = 0\text{ V}; T_j = 25\text{ }^\circ\text{C};$ <a href="#">Fig. 15</a>	-	0.8	1	V	
$t_{rr}$	reverse recovery time	$I_S = 20\text{ A}; di_S/dt = -100\text{ A}/\mu\text{s}; V_{GS} = 0\text{ V};$ $V_{DS} = 15\text{ V};$ <a href="#">Fig. 16</a>	-	28	-	ns	
$Q_r$	recovered charge		[1]	-	22	-	nC
$t_a$	reverse recovery rise time		-	-	16.4	-	ns
$t_b$	reverse recovery fall time		-	-	11.2	-	ns
S	softness factor		-	-	0.7	-	

[1] includes capacitive recovery

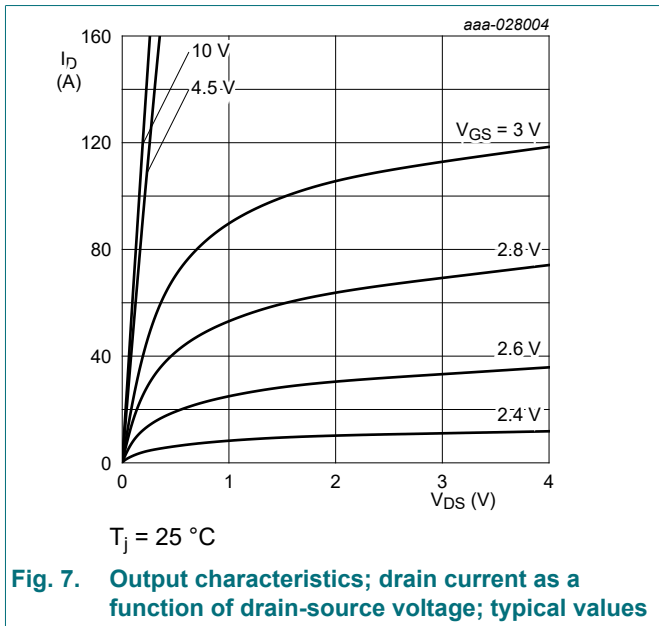


Fig. 7. Output characteristics; drain current as a function of drain-source voltage; typical values

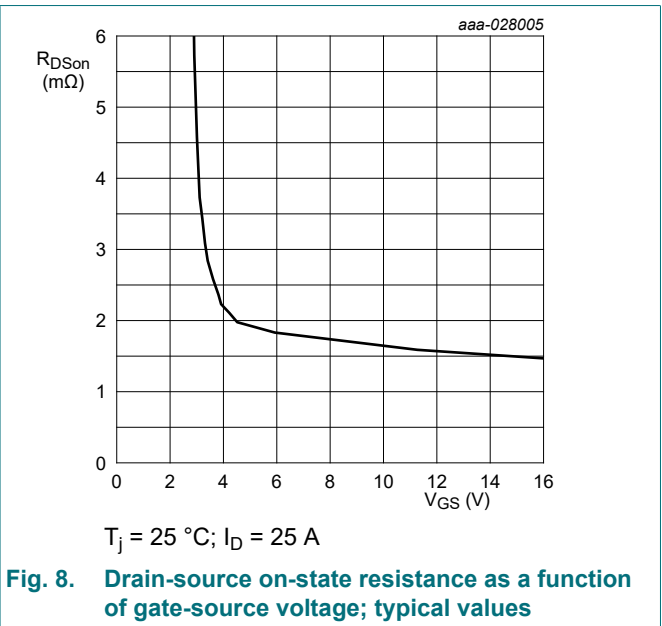


Fig. 8. Drain-source on-state resistance as a function of gate-source voltage; typical values

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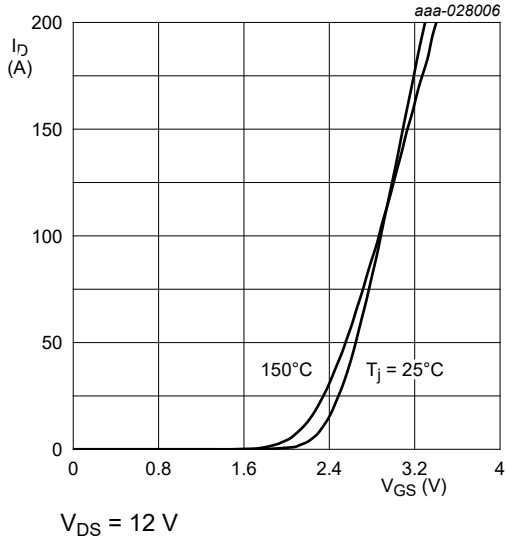


Fig. 9. Transfer characteristics; drain current as a function of gate-source voltage; typical values

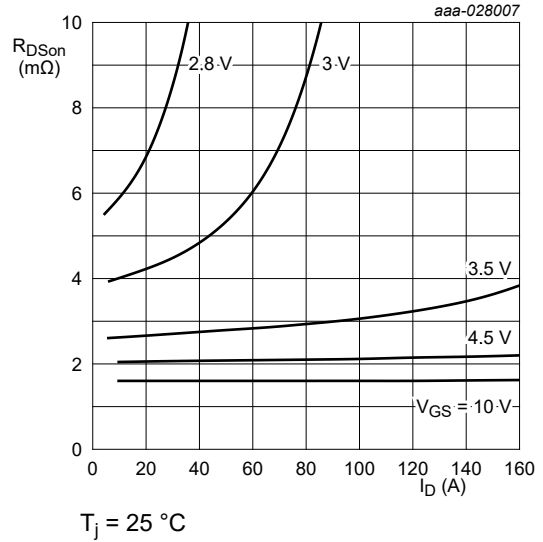
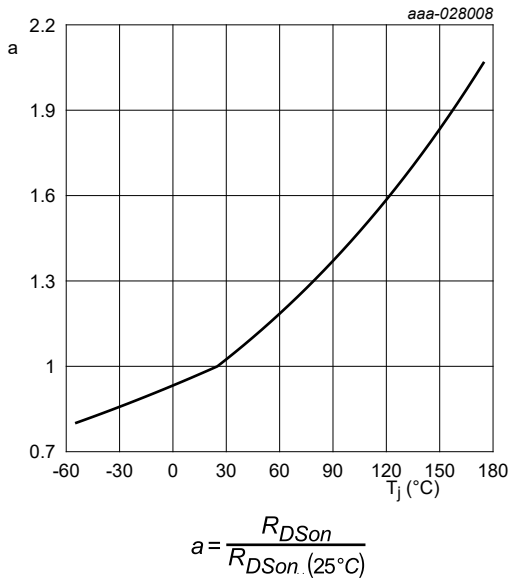


Fig. 10. Drain-source on-state resistance as a function of drain current; typical values



$$a = \frac{R_{DSon}}{R_{DSon}(25^\circ\text{C})}$$

Fig. 11. Normalized drain-source on-state resistance factor as a function of junction temperature

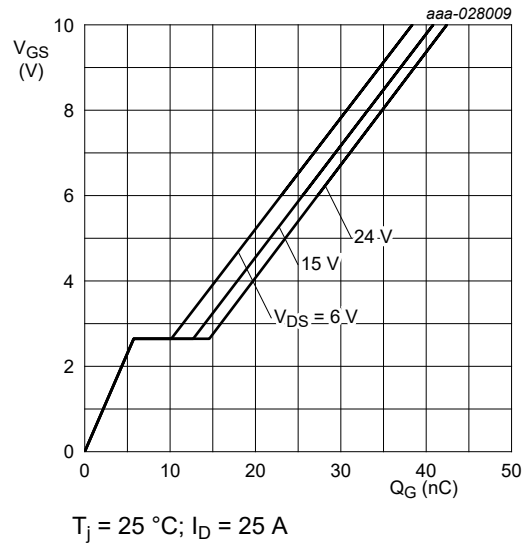


Fig. 12. Gate-source voltage as a function of gate charge; typical values

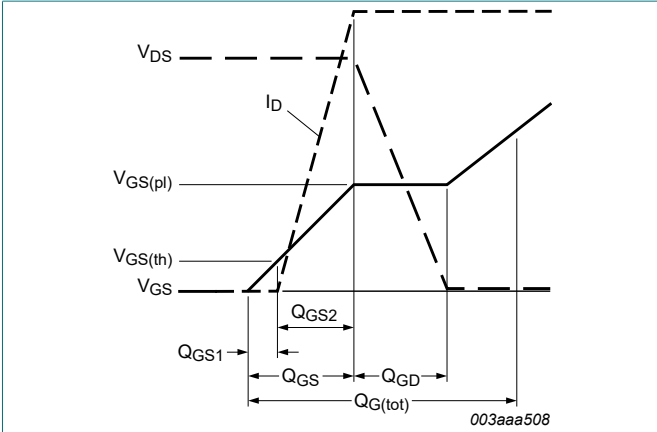


Fig. 13. Gate charge waveform definitions

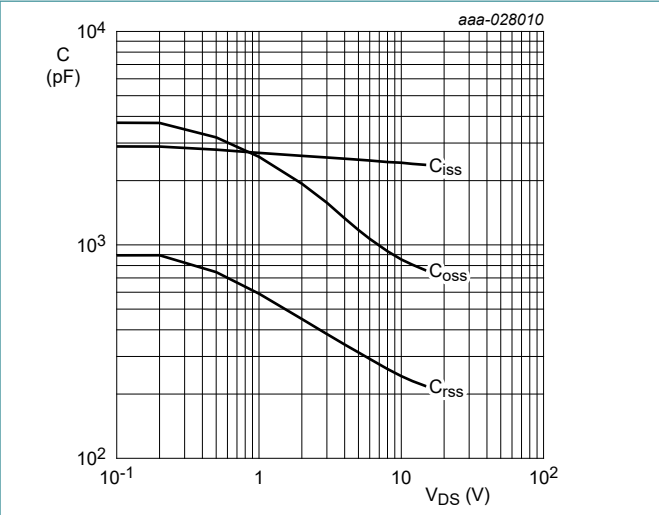


Fig. 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

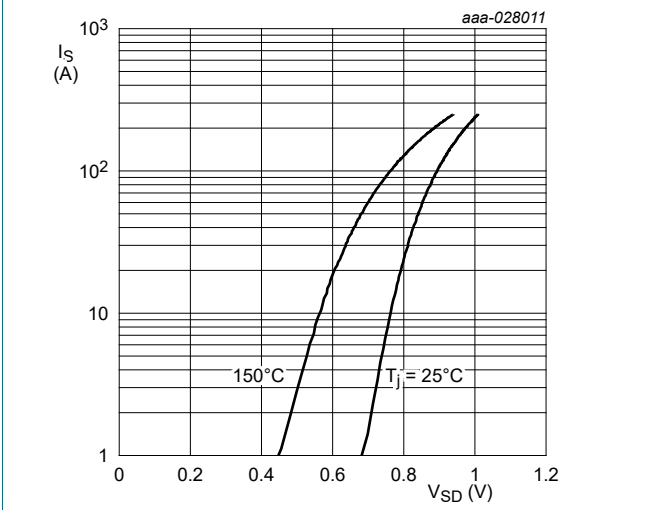


Fig. 15. Source-drain (diode forward) current as a function of source-drain (diode forward) voltage; typical values

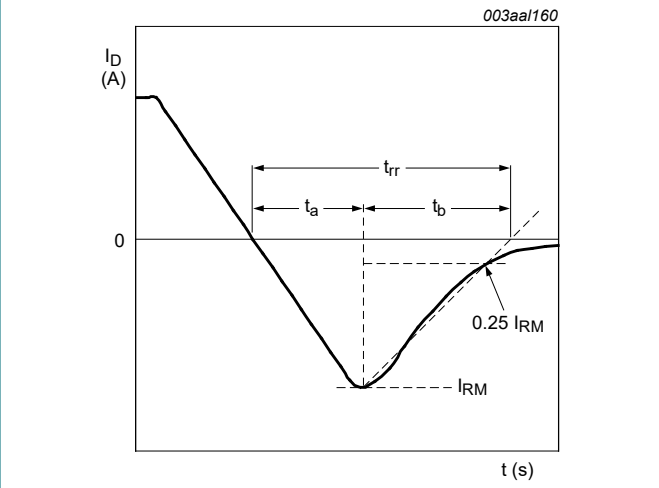


Fig. 16. Reverse recovery timing definition

### 11. Package outline

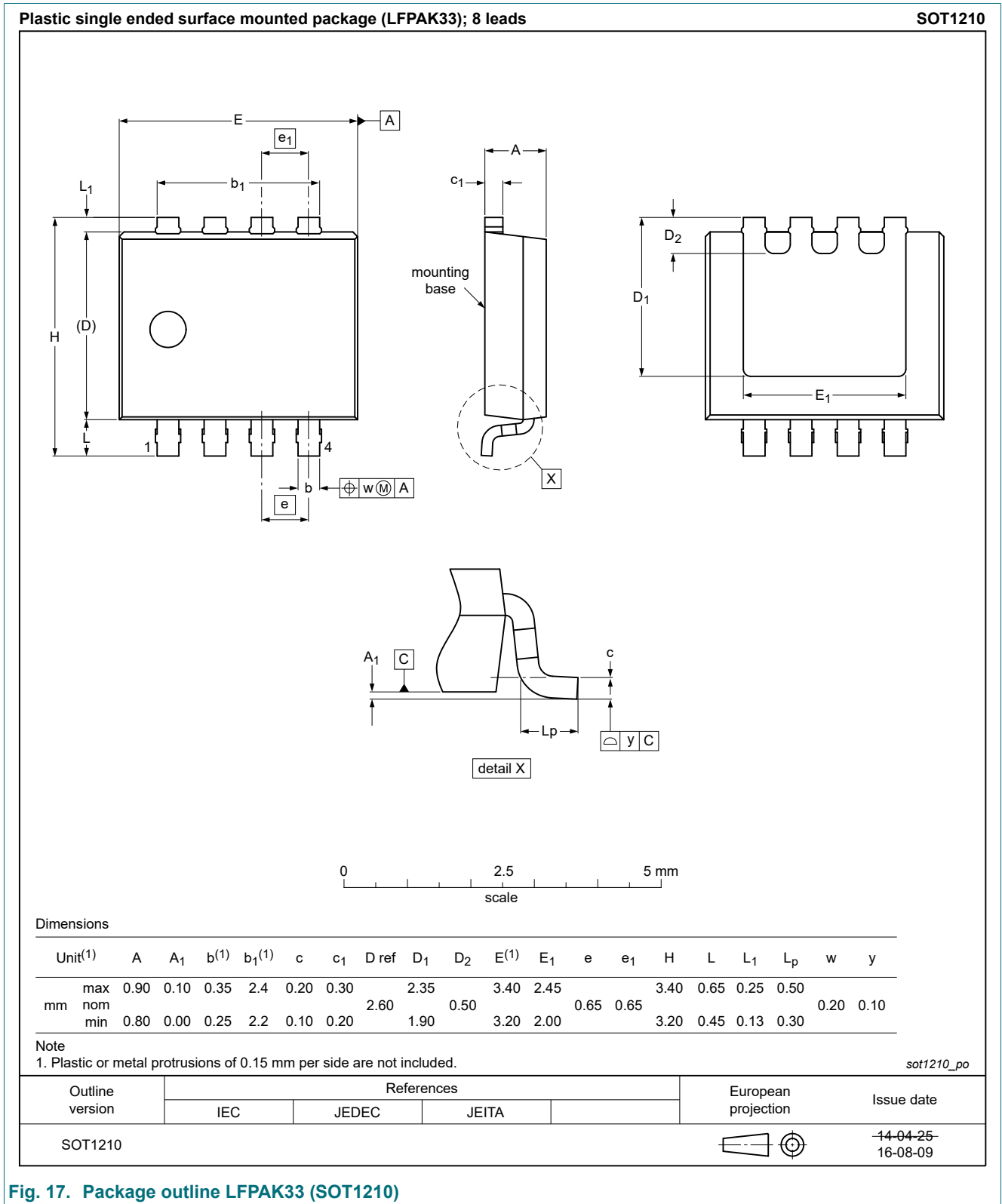
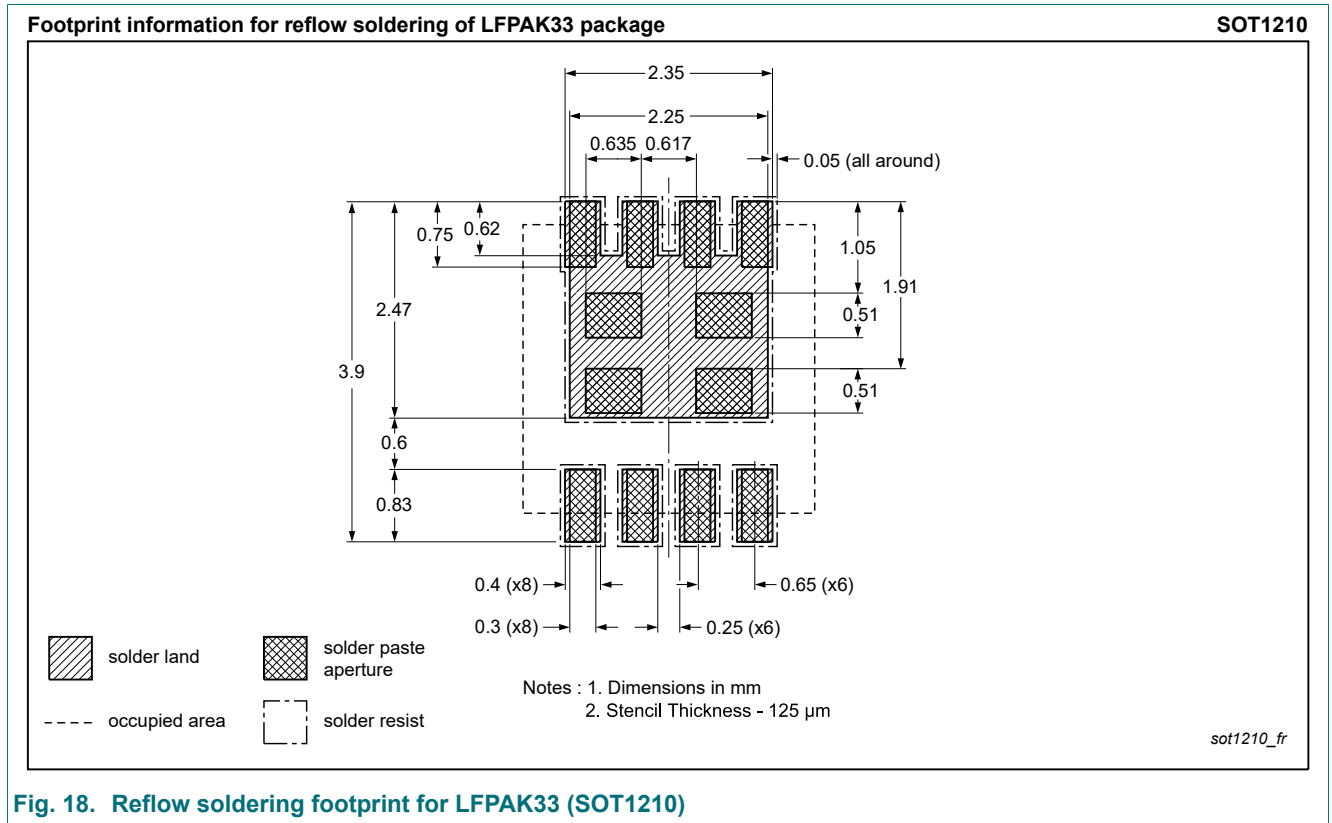


Fig. 17. Package outline LPAK33 (SOT1210)

## 12. Soldering



**Fig. 18. Reflow soldering footprint for LPAK33 (SOT1210)**

## 13. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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-  Obsolete Management
-  Cost Control Management
-  Shortage Management
-  Alternative Solution
-  Excess Inventory Management